

<b>Notice of References Cited</b>	Application/Control No. 09/761,753	Applicant(s)/Patent Under Reexamination ISHIDA ET AL.	
	Examiner Fernando Toledo	Art Unit 2823	Page 1 of 1

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**NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Ghandhi, Sorab; VLSI Fabrication Principles Silicon and Gallium Arsenide, Second Ed., Jhon Wiley & Sons, Inc. page 641
	V	Merriam Webster's Collegiate Dictionary 10th Edition, Merriam Webster Inc. page 254
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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
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